

**AMENDMENTS TO THE SPECIFICATION:**

Please replace the paragraph on page 7, lines 6-13 with the following paragraph:

As illustrated in Figure 2, subsequently the etching mask 12 is removed from the front side, which has just been microstructured, of the silicon wafer 11, the wafer 11 is turned, the rear side of the silicon wafer 11 is then masked photo-lithographically with an etching mask 14 and subsequently it is structured by means of drying etching according to the above described method, wherein this time the structures are driven through the wafer 11 (hereinafter referred to as 'through-etching') and thus an arrangement of cavities 15 is produced which have an first orifice 16 on the front side of the wafer 11 and ~~an~~ a second orifice 17 on the rear side of the wafer 11 respectively.